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**Spin transport over long distance in epitaxial graphene grown on C-face SiC**

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Spintronics is a paradigm focusing on spin as the information vector and ranging from quantum information to zero-power non-volatile magnetism. Several spintronics evices (logic gates, spin FET, etc) are based on spin transport in a lateral channel between spin polarized contacts. However while spin is acclaimed for information storage, a paradox is that efficient spin transport as remained elusive. We will present magneto-transport experiments on epitaxial graphene multilayers on SiC showing very large spin signals and spin diffusion length in graphene in the  $100\mu\text{m}$  range (as high as  $285\mu\text{m}$ ). In the best case, the spin transport efficiency of epitaxial graphene is found to be of 75% of the ideal channel. Graphene, could turn out as a material of choice for large scale logic circuits and the transport/processing of spin information. Understanding the mechanism of the spin relaxation, improving the spin diffusion length and also testing various concepts of spin gates are the next challenges.

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References:

Dlubak et al. Nature Phys 8 557 (2012)

Seneor et al. MRS Bulletin 37 1245 (2012)